

## Features

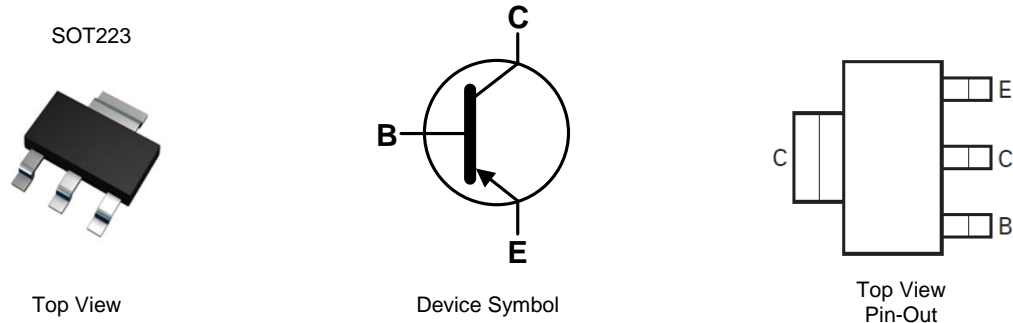
- $BV_{CEO} > -150V$
- $I_C = -600mA$  high Collector Current
- Ideal for Medium Power Switching or Amplification Applications
- Complementary PNP Type: DZT5551
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 Ⓔ
- Weight: 0.112 grams (Approximate)

## Applications

- Amplifiers
- Power Supplies

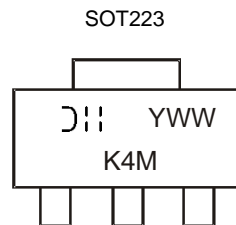


## Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DZT5401-13	Standard	K4M	13	12	2,500

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



K4M = Product Type Marking Code  
 DII = Manufacturer's Code Marking  
 YWW = Date Code Marking  
 Y = Last Digit of Year (ex: 7 = 2017)  
 WW = Week Code (01 to 52)

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Collector Current	I <sub>C</sub>	-600	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation @T <sub>A</sub> = +25°C	(Note 5) P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C	(Note 5) R <sub>θJA</sub>	125	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

**ESD Ratings** (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the collector lead on minimum recommended pad (MRP) layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

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### Thermal Characteristics and Derating Information

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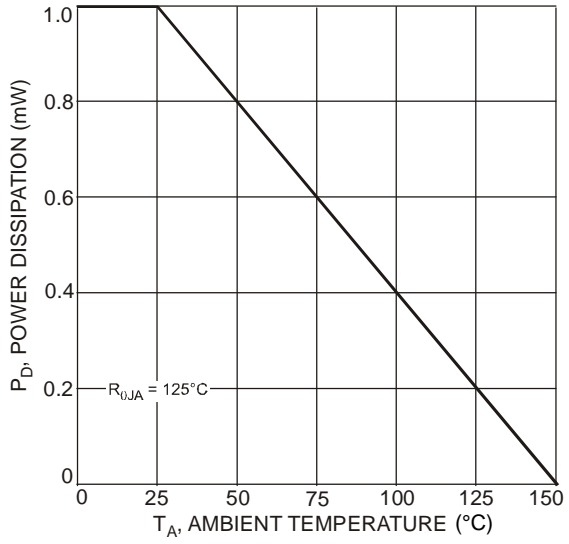


Fig. 1 Max Power Dissipation vs. Ambient Temperature

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-160	—	—	V	I <sub>C</sub> = -100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 7)	BV <sub>CEO</sub>	-150	—	—	V	I <sub>C</sub> = -1mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	—	—	V	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0
Collector-Base Cut-off Current	I <sub>CBO</sub>	—	—	-50	nA	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0
Emitter-Base Cut-off Current	I <sub>EBO</sub>	—	—	-50	nA	V <sub>EB</sub> = -3V, I <sub>C</sub> = 0
<b>ON CHARACTERISTICS (Note 7)</b>						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	—	-0.2 -0.5	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	—	-1.0	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5mA
Static Forward Current Transfer Ratio	h <sub>FE</sub>	50 60 50	—	— 240 —	—	I <sub>C</sub> = -1mA, V <sub>CE</sub> = -5V I <sub>C</sub> = -10mA, V <sub>CE</sub> = -5V I <sub>C</sub> = -50mA, V <sub>CE</sub> = -5V
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Transition Frequency	f <sub>T</sub>	100	—	300	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -10mA, f = 100MHz
Output Capacitance	C <sub>obo</sub>	—	—	6	pF	V <sub>CB</sub> = -10V, f = 1MHz, I <sub>E</sub> = 0
Small Signal Current Gain	h <sub>FE</sub>	40	—	260	—	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1.0mA, f = 1.0kHz
Noise Figure	NF	—	—	8	dB	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -200μA, R <sub>S</sub> = 10Ω, f = 1.0kHz

Note: 7. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

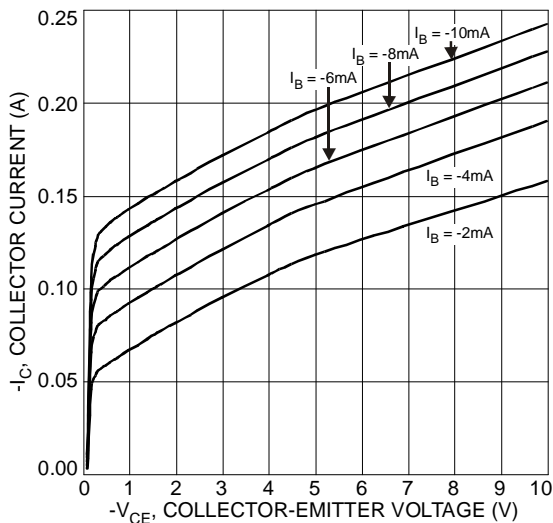


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

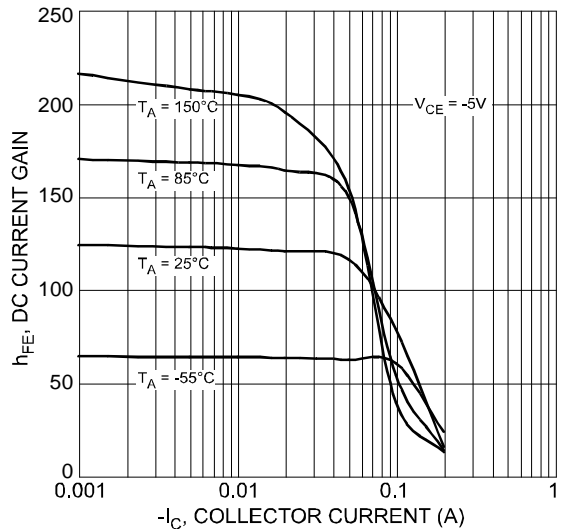


Fig. 3 Typical DC Current Gain vs. Collector Current

**Typical Electrical Characteristics (Cont.)**

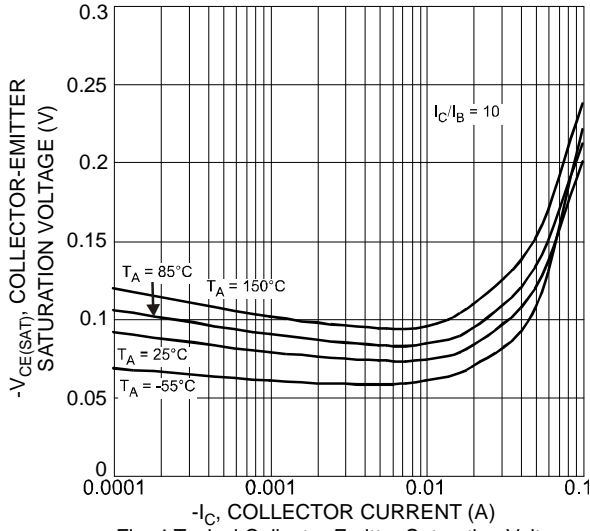


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

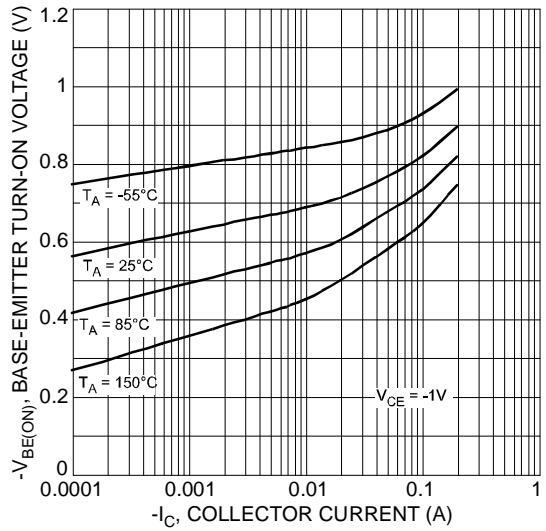


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

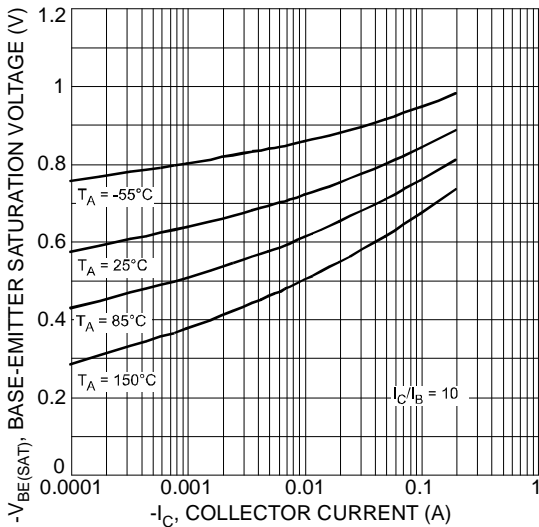


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

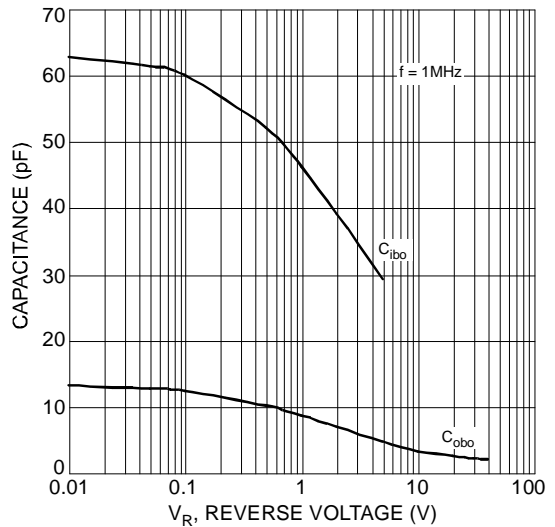


Fig. 7 Typical Capacitance Characteristics

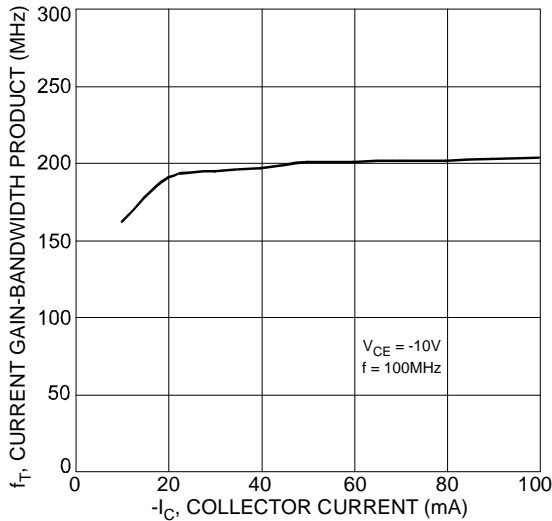
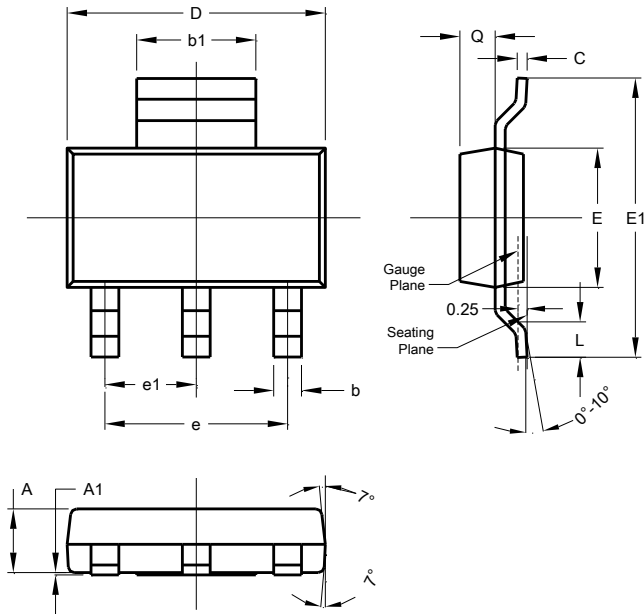


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT223**

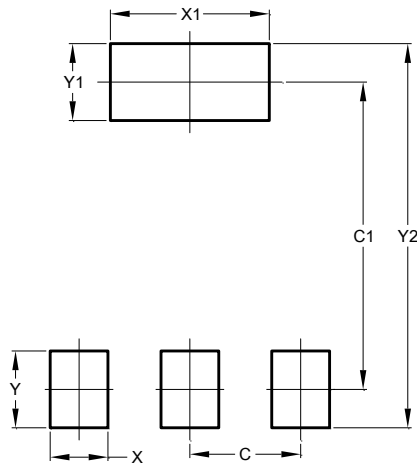


SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT223**



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

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